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Docket No.: EHF 2001,0167 P

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By: Jm P. ~

Date: 8/3/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Norbert Benesch et al.
Applic. No. : 09/873,230
Filed : June 4, 2001
Title : Method and Device for Optically Monitoring Fabrication Processes of Finely Structured Surfaces in a Semiconductor Production

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

United States Patent No. 5,768,192 (Eitan), dated June 16, 1998;

United States Patent No. 6,011,725 (Eitan), dated January 4, 2000;

United States Patent No. 6,191,459 B1 (Hofmann et al.), dated February 20, 2001;

German Patent DE 196 00 422 C1 (Krautschneider et al.), dated August 21, 1997,
electric programmable memory cell configuration and method for its production;

German Patent DE 196 03 810 C1 (Krautschneider et al.), dated August 28, 1997,
memory cell configuration and method for its production;



AUG 06 2001

German Published, Non-Prosecuted Patent Application DE 195 45 903 A1

German Published, Non-Prosecuted Patent Application DE 196 00 423 A1 (Hofmann et al.), dated July 17, 1997, electric programmable memory cell configuration and method for its production;

German Published, Non-Prosecuted Patent Application DE 196 00 423 A1 (Hofmann et al.), dated July 17, 1997, electric programmable memory cell configuration and method for its production;

International Publication WO 99/60631 (Eitan), dated November 25, 1999;

Junko Tanaka et al.: "A Sub-0.1- μ m Grooved Gate MOSFET with High Immunity to Short-Channel Effects", IEDM 93, pp. 537-540;

Ken-ichiro Nakagawa et al.: "A Flash EEPROM Cell with Self-Aligned Trench Transistor & Isolation Structure", 2000 Symposium on VLSI Technology Digest of Technical Papers.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,


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For Applicants

Date: August 3, 2001

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